SONY

1/3 inch CCD Image Sensor for CCIR B/W Camera

Description

The ICX059ALB is an interline transfer CCD solid-state image sensor suitable for CCIR B/W video cameras. High sensitiveness and low dark current are achieved through the adoption of HAD (Hole-Accumulation Diode) sensors.

This chip features a field integration read out system and an electronic shutter with variable charge-storage time. Also, this outline is miniaturized by using original package.

Features

- · High image, high sensitivity and low dark current
- · Consecutive various speed shutter
- 1/50s (Typ.), 1/120s to 1/10000s
- · Low smear
- High antiblooming
- Horizontal register 5V drive
- Reset gate 5V drive

Device Structure

- Optical size
- 1/3-inch format

1(even field only)

- Number of effective pixels 752 (H)×582 (V) Approx. 440k pixels
- Number of total pixels
 795 (H)×596 (V) Approx. 470k pixels
- Interline transfer CCD image sensor
- Chip size 6.00mm (H) × 4.96mm (V)
- · Until cell size 6.5 μ m (H)×6.25 μ m (V)

 Optical black Horizontal (H) direction Vertical (V) direction
 Number of dummy bits: Horizontal
 Front 3 pixels Rear 40 pixels
 Front 12 pixels Rear 2 pixels
 22

Vertical

Board material:

al: N-type silicon

 $\begin{array}{c} Pin 1 \\ \downarrow \\ \downarrow \\ \downarrow \\ \downarrow \\ 3 - \downarrow \\ Pin 8 \end{array} \xrightarrow{(H)} H \xrightarrow{(H)} 40 \end{array}$

Optical black position (Top View)

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<u>ICX059ALB</u>



Block Diagram (Top View)





Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	V ø 4	Vertical register transfer clock	8	Vdd	Output amplifier drain supply
2	V ø 3	Vertical register transfer clock	9	GND	GND
3	V ø 2	Vertical register transfer clock	10	SUB	Substrate (Overflow drain)
4	V ø 1	Vertical register transfer clock	11	VL	Protective transistor bias
5	Vaa	Output amplifier gate bias	12	RG	Reset gate clock
6	Vss	Output amplifier source	13	Høı	Horizontal register transfer clock
7	Vout	Signal output	14	Hø2	Horizontal register transfer clock

Absolute Maximum Ratings

	ltem	Ratings	Unit	Remarks
Substrate voltage	SUB-GND	-0.3 to +55	V	
Supply valtage	VDD, VOUT, VSS-GND	-0.3 to +18	V	
Supply voltage	VDD, VOUT, VSS - SUB	-55 to +10	V	1
Vertical clock	V \$ 1, V \$ 2, V \$ 3, V \$ 4 - GND	-15 to +20	V	
input voltage	V \$ 1, V \$ 2, V \$ 3, V \$ 4 - SUB	to +10	V	
Voltage difference	between vertical clock input pins	to +15	V	*
Voltage difference	between horizontal clock input pins	to +17	V	
H ø 1, H ø 2 – V ø 4		-17 to +17	V	
H \$ 1,H \$ 2,RG,VGG	- GND		V	
H \$\$ 1,H \$\$ 2,RG,VGG	- SUB	55 to + 10	V	
VL - SUB		-65 to +0.3	V	
V ø 1, V ø 2, V ø 3, V	φ 4 , Vdd, Vout — Vl	-0.3 to +30	V	
RG – VL		-0.3 to +24	V	
VGG, Vss, H ø 1, H ø	2 - VL	-0.3 to +20	V	
Storage temperatu	re	-30 to +80	°C	
Operating temperat	ure	-10 to +60	°C	

* +27V(Max.) when clock width < 10 μ s, duty factor < 0.1%.

— 2 —

Bias Conditions

ltem	Symbol	Min.	Тур.	Max.	Unit	Remarks
Output amplifier drain voltage	Voo	14.55	15.0	15.45	V	
Output amplifier gate voltage	Veg	3.8	4.2	4.65	V	
Output amplifier source	Vss	Gr 82	ound throi 0 Ω resist	ugh or		±5%
Substrate voltage adjustment range	Vsue	9.0		18.5	V	*2
Fluctuation range after substrate voltage adjustment	∆ Vsu8	3		+3	%	
Reset gate clock voltage adjustment range	Vrgl	1.0		4.0	V	*2 *6
Fluctuation range after reset gate clock voltage adjustment		-3		+3	%	
Protective transistor bias	V.	I	*3	I		

DC Characteristics

ltem	Symbol	Min.	Тур.	Max.	Unit	Remarks
Output amplifier drain current	loo		5		mA	
Input current	lini	-		1	μA	*4
Input current	lin2			10	μA	*5

* 2 Substrate voltage (Vsue) · reset gate clock voltage (VRGL) setting value display. Setting values of substrate voltage and reset gate clock voltage are displayed at the back of the device through a code address. Adjust substrate voltage (Vsue) and reset gate clock voltage (VRGL) to the displayed voltage. Fluctuation range after adjustment is ±3%.

Vsue code address - 1 digit display Vect code address - 1 digit display ▲____`

Vsue address code

9.0 9.5 10.0 10.5 11.0 11.5 12.0 12.5 13.0 13.5 14.0 14.5 15.0 15.5 16.0 16.5 17.0 17.5 18.0 18.5

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Code addresses and actual numerical values correspond to each other as follows.

VRGL addres	s co	je		1	2	3	4 !	5 6	7	٦					-	
Numerical v	alue			1.0	1.5	2.0 2	2.5 3	.0 3.	5 4.(2						
Vsue address code	E	f	G	h	J	ĸ	L	m	N	Р	٩	R	s	т	υ	v
Numerical	9.0	95	10.0	10.5		0 11 F	120	125	120	125	140	115	15.0	15.5	16.0	16.5

<Example> "5L" \rightarrow V_{RGL} = 3.0V

V_{SUB} = 12.0V

value

* 3 VL setting is the VvL voltage of the vertical transfer clock waveform.

— 3 —

- * 4 1. Current to each pin when 18V is applied to Voo, Vout, Vss and SUB pins, while pins that are not tested are grounded.
 - 2. Current to each pins when 20V is applied sequentially to $V \neq 1$, $V \neq 2$, $V \neq 3$ and $V \neq 4$, while pins that are not tested are grounded. However, 20V is applied to SUB.
 - 3. Current to each pins when 15V is applied sequentially to pins RG, H \u03c6 1, H \u03c6 2 and V_{GG}, while pins that are not tested are grounded. However, 15V is applied to SUB.
 - Apply 30V to Pins V φ 1, V φ 2, V φ 3, V φ 4, V_{DD}, V_{OUT}; 24V to Pin RG; and 20V to Pins V_{GG}, V_{SS}, H φ 1, H φ 2. The above is the current that flows to Pin V_L when it is grounded. Please note that Pins GND and SUB are to be disconnected.
- * 5 Current to SUB pin when 55V is applied to SUB pin, while pins that are not tested are grounded.

ltem	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Read out clock voltage	Vvt	14.55	15.0	15.45	v	1	
	Vvh1, Vvh2	-0.05	0	0.05	V	2	Vvh= (Vvh1+Vvh2)/2
	Vvh3, Vvh4	-0.2	0	0.05	V	2	
	Vvl1, Vvl2, Vvl3, Vvl4	-9.0	-8.5	-8.0	V	2	Vvl= (Vvl3+Vvl4)/2
	Vøv	7.8	8.5	9.05	v	2	$V \neq v = V_{VHn} - V_{VLn}$ (n=1 to 4)
Vertical transfer clock	Vvh1, Vvh2			0.1	V	2	· · · · · · · · · · · · · · · · · · ·
voltage	Vvh3 — Vvh	-0.25		0.1	V	2	
	Vvh4 – Vvh	-0.25		0.1	V	2	
	Vvнн			0.5	V	2	High level coupling
	Vvhl			0.5	V	2	High level coupling
	Vvlh			0.5	V	2	Low level coupling
·	Vvll			0.5	V	2	Low level coupling
Horizontal transfer	Vфн	4.75	5.0	5.25	V	3	
clock voltage	Vhl	-0.05	. 0	0.05	V	3	
Reset gate clock	V ¢ rg	4.5	5.0	5.5	V	4	*6
voltage		<u>e</u> .		0.8	V	4	Low level coupling
Substrate clock voltage	V ¢ sue	22.5	23.5	24.5	v	5	

Clock Voltage Conditions

* 6 No adjustment of reset gate clock voltage is necessary when reset gate clock is driven as indicated below. In this case, reset gate clock voltage set point displayed on back of image sensor has no meaning.

ltem	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Reset gate clock		-0.2	0	0.2	V	4	
voltage	V ¢ AG	8.5	9.0	9.5	V	4	· · · · · · · · · · · · · · · · · · ·

- 4 --

Clock Equivalent Circuit Constant

ltem	Symbol	Min.	Тур.	Max.	Unit	Remarks
Capacitance between vertical transfer	С ф v1, С ф v3		1000		pF	
clock and GND	C \$ v2, C \$ v4		560	[pF	
	C \$ V12, C \$ V34	ſ	470		pF	
Capacitance between vertical transfer	C \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$ \$		390		ρF	
clocks	C ¢ v13		180		pF	
	C \$ V24		100		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		47		ρF	
Capacitance between horizontal transfer clocks	Сфин		51		рF	
Capacitance between reset gate clock and GND	C ¢ RG		8		рF	
Capacitance between substrate clock and GND	С ф ѕив		270		pF	
Vertical transfer clock serial resistor	R1, R2, R3, R4		80		Ω	
Vertical transfer clock ground resistor	Rgnd		15		Ω	
Horizontal transfer clock serial resistor	Røн		15		Ω	



Vertical transfer clock equivalent circuit



Horizontal transfer clock equivalent circuit

Drive Clock Waveform Conditions

(1) Read out clock waveform



(2) Vertical transfer clock waveform



 $V_{VH} = (V_{VH1} + V_{VH2})/2$ $V_{VL} = (V_{VL3} + V_{VL4})/2$ $V_{\phi V} = V_{VHn} - V_{VLn} (n = 1 \text{ to } 4)$

— 6 —

(3) Horizontal transfer clock waveform diagram



(4) Reset gate clock waveform diagram



VRGLH is the maximum value and VRGLL the minimum value of the coupling waveform in the period from Point A in the diagram above to RG rise.

VRGL is the mean value for VRGLH and VRGLL.

VRGL =(VRGLH + VRGLL)/2

VRGH is the minimum value for twh period.

VARG = VAGH-VRGL

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(5) Substrate clock waveform



Clock Switching Characteristics

	ltem	Symbol	Ĺ	twh			twf			tr			tf		[
			Min.	Тур.	Max.	Unit	Remarks										
Read	j out clock	VT	2.3	2.5						0.5			0.5		μs	During read ou	
Vertic clock	cal transfer	V φ 1, V φ 2, V φ 3, V φ 4		+							 	15		250	ns	*7	
b During		Ηφι	18	24		19.5	26			10	17.5		10	17.5			
tran. K	imaging	Ηφε	21	26		19	24			10	15		10	15	ns	*8	
Horizontal transfer clock	During parallel	Ηφı		6.41		-				0.01			0.01				
Horiz	serial conversion	Ηφ2					6.41			0.01			0.01		μs		
Rese	t gate clock	φ RG	11	13			51			3			3		ns	<u> </u>	
Subs	trate clock	¢ sub	1.5	1.8							0.5			0.5	μs	During charge drain	

* 7 When vertical transfer clock driver CXD1250 is in use.

* 8 tf≥tr-2 ns, and the crosspoint voltage (VcR) of the H φ₁ rise side of waveforms H φ₁ and H φ₂ must be at least 2.5V.

ltem	Symbol		two		Link	Remarks	
		Min,	Тур.	Max.	UIIA	nemarks	
Horizontal transfer clock	Hø1, Hø2	16	20		ns	*9	

* 9 "two" is the overlap period of horizontal transfer clocks H ϕ_1 and H ϕ_2 's twh and twl.

— 8 —

Operating Characteristics

Operating Charact	eristics						(Ta=25℃
Item	Symbol	Min.	Тур.	<u>M</u> ax.	Unit	Test method	Remarks
Sensitivity	S	240	300		mV	1	
Saturation signal	Vsat	540		· · · · · · · · · · · · · · · · · · ·	mV	2	Ta=60°C
Smear	Sm		0.009	0.015	%	3	
Video signal shading	SH			20	%	4	Zone 0, I
				25	%	4	Zone 0 to II '
Dark signal	Vdt			2	mV	5	Ta=60°C
Dark signal shading	∆Vdt			1	mV	6	Ta=60°C
Flicker	F			2	%	7	
Lag	Lag			0.5	%	8	

Zone Chart of Video Signal Shading



Image Sensor Characteristics Test Method

OTest conditions

- ()Through the following tests the substrate voltage and reset gate clock voltage are set to the value displayed on the device, while the device drive conditions are the typical value of the bias and clock voltage conditions.
- (2) Through the following tests defects are excluded and, unless otherwise specified, the optical black level (Hence forth referred to as OB) is set as the reference, the values obtained at (A) point in the figure of the Drive Circuit are utilized.

- 9 ---

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ODefinition of standard imaging conditions

①Standard imaging condition I :(As imaging device) Use a pattern box (luminance 706 cd/m², color temperature 3200K Halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t =1.0mm) as IR cut filter and image at F8. At this time, light intensity to sensor receiving surface is defined as standard sensitivity testing light intensity.

②Standard imaging condition II: Image a light source (color temperature of 3200K) which uniformity of brightness is within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as IR cut filter. The light intensity is adjusted to the value indicated in each testing item by lens diaphragm.

1. Sensitivity

Set to standard image condition I. After selecting the electronic shutter mode at a 1/250s. shutter speed, measure the signal output (Vs) at the center of the screen and substitute in the following formula.

$$S = V_s \times \frac{250}{50} [mV]$$

2. Saturation signal

Set to standard imaging condition II. Adjust light intensity to 10 times that of signal output average value (Va=200mV), then test signal minimum value.

3. Smear

Set to standard imaging condition II. Adjust light intensity to 500 times that of signal output average value (V_A=200mV) with lens diaphragm at F5.6 to F8. Stop read out clock. When the charge drain executed by the electronic shutter at the respective H blankings takes place, test the maximum value VSm [mV] of signal output.

$$Sm = \frac{VSm}{200} \times \frac{1}{500} \times \frac{1}{10} \times 100(\%)(1/10V)$$

4. Video signal shading

Set to standard imaging condition II. Adjust light intensity to signal output average value (V_A=200mV) with lens diaphragm at F5.6 to F8. Then test maximum (Vmax [mV]) and minimum (Vmin [mV]) values of signal output.

SH=(Vmax - Vmin)/200 × 100(%)

5. Dark signal

Test signal output average value Vdt [mV] when the device ambient temperature is at 60°C and light is obstructed with horizontal idle transfer level as reference.

6. Dark signal shading

Following 5, test maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of dark signal output.

 Δ Vdt = Vdmax – Vdmin [mV]

-10-

7. Flicker

Set to standard imaging condition II. Adjust light intensity to signal output average value (V_A=200mV). Then test the signal difference (Δ Vf (mV)) between even field and odd field. F=(Δ Vf/200)×100(%)

8. Residual image

Adjust signal output value by strobe light to 200mV. Then light a stroboscopic tube with the following timing and test the residual image (Vlag).

Lag = (Vlag \checkmark 200) \times 100 (%)



- 11 ---







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3.3/16 /

Spectral Sensitivity Characteristics

(Excluding light source characteristics, including lens characteristics)



Using Read Out Clock Timing Chart



Unit: µs

3370 3370 3370 3370 3370 3370 3370 3370		
FLD FLD FLD FLD FLD FLD FLD FLD	sgiSg2	v: [] [] [] [] [] [] [] [] [] [] [] [] []

Drive Timing Chart (Vertical sync)

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sync)
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Chart (H
Timing
Drive

		UNUUVEDDAWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWW	асти и полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили странатили пол В Странатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили. В Странатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили полнатили. В Стран					
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Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates use boxes treated for the prevention of static charges.

2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a grounded 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an imaging device do not use a solder suction equipment. When using an electric desoldering tool use a thermal controller of the zero cross On/Off type and connect to ground.
- 3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Operate in clean environments (around class 1000 will be appropriate).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface blow it off with an air blow. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the glass surface is grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Do not expose to strong light (sun rays) for long periods.

For continuous using under cruel condition exceeding the normal using condition, consult our company.

- 5) Exposure to high temperatures or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- 6) CCD image sensor are precise optical equipment that should not be subject to too much mechanical shocks.
- 7) Eclipse (to get dark around the four corners of the picture) may occur when some object lenses are in the open ins state.



Unit: mm Package Outline





POTEOL .

1.84

2.5

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1. Aは有効撮像エリアの中心

9.5±0.2

9.15

4.75

1PIN Index

- **垂直方向の基準はパッケージ動画 B*** 2. 水平方向の基準はパッケージ側面B
 - 高さ方向の基準はパッケージ底面C đ
- パッケージ中心に対する有効損後エリアの中心位置度公差±0.15mm
 - H、V方向に対する有効振復面の回転傾度:上1
 - 底面Cから有効提後面までの高さ:1.41±0.15mm
 - 底面Cに対する有効損像面のアオリ:60μm以下
- 8. シールガラスの厚さは0.75mm(実寸)、屈訴率は1.5

★バッケージ中心:バッケージ舞画B、 B' にそれぞれ対向し合う2組の雑画により 得られる中心点

- "A" Is the center of the effective image area.
- The point "B" of the package is the horizontal relevance. The point "B" of the package is the vertical reference. 2
 - The bottom "C" of the package is the height reference.
- The center of the effective image area relative to the center of the package(\star) Is (H. V) =(0,0)±0.15mm.
 - The rotation angle of the effective image area relative to H and V is $\pm 1^\circ$, vi
- The height from the bottom "C" to the effective image area is 1.41 \pm 0.15mm.
- 7. The tilt of the effective image area relative to the bottom "C" is less than 60 μ m.
 - The trickness of the cover glass is 0.75mm, and the retractive index is 1.5.
- * Center of the package : The conter is halfway between two pairs of opposite sides, as measured from "B", "B".

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ICX059ALB
IOV033VFD





PACKAGE STRUCTURE

Ceramic	GOLD PLATING	42 ALLOY	0.6g
PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE WEIGHT